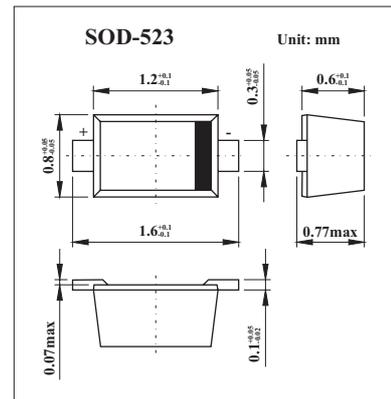


Switching Diode

1SS400

■ Features

- High Speed Switching ($t_{rr} = 1.2\text{ns}$)
- Extremely Small Surface Mounting Type
- High Reliability
- Silicon Epitaxial Planar

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Peak Forward Current	I_{FM}	225	mA
Mean Rectifying Current	I_o	100	mA
Surge Current (1s)	I_{surge}	500	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 100\text{mA}$			1.2	V
Reverse Current	I_R	$V_R = 80\text{V}$			0.1	μA
Capacitance Between Terminals	C_T	$V_R = 0.5\text{V}$, $f = 1\text{MHz}$		0.72	3.0	pF
Reverse Recovery Time	t_{rr}	$V_R = 6\text{V}$, $I_F = 10\text{mA}$, $R_L = 100\Omega$			4	ns

■ Marking

Marking	A
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